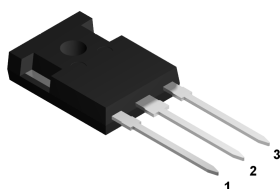
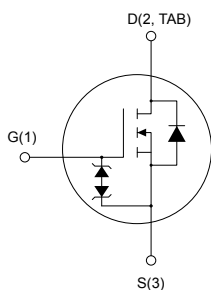


## Automotive-grade N-channel 600 V, 37 mΩ typ., 66 A MDmesh DM2 Power MOSFET in a TO-247 long leads package



TO-247 long leads




AM01476v1\_tab



### Features

Order code	$V_{DS}$	$R_{DS(on)}$ max.	$I_D$
STWA72N60DM2AG	600 V	42 mΩ	66 A

- AEC-Q101 qualified 
- Fast-recovery body diode
- Extremely low gate charge and input capacitance
- Low on-resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected

### Applications

- Switching applications

### Description

This high-voltage N-channel Power MOSFET is part of the MDmesh DM2 fast-recovery diode series. It offers very low recovery charge ( $Q_{rr}$ ) and time ( $t_{rr}$ ) combined with low  $R_{DS(on)}$ , rendering it suitable for the most demanding high-efficiency converters and ideal for bridge topologies and ZVS phase-shift converters.

#### Product status link

[STWA72N60DM2AG](#)

#### Product summary

Order code	STWA72N60DM2AG
Marking	72N60DM2
Package	TO-247 long leads
Packing	Tube

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	66	A
	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	42	
$I_{DM}^{(1)}$	Drain current (pulsed)	220	A
$P_{TOT}$	Total dissipation at $T_{case} = 25\text{ }^{\circ}\text{C}$	446	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	50	V/ns
$dv/dt^{(3)}$	MOSFET $dv/dt$ ruggedness	50	V/ns
$T_{stg}$	Storage temperature range	-55 to 150	$^{\circ}\text{C}$
$T_J$	Operating junction temperature range		$^{\circ}\text{C}$

1. Pulse width is limited by safe operating area.
2.  $I_{SD} \leq 66\text{ A}$ ,  $V_{DS} (\text{peak}) < V_{(BR)DSS}$ ,  $di/dt = 800\text{ A}/\mu\text{s}$ ,  $V_{DD} = 480\text{ V}$ .
3.  $V_{DS} \leq 480\text{ V}$

**Table 2. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thJC}$	Thermal resistance, junction-to-case	0.28	$^{\circ}\text{C}/\text{W}$
$R_{thJA}$	Thermal resistance, junction-to-ambient	50	$^{\circ}\text{C}/\text{W}$

**Table 3. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive (pulse width limited by $T_J$ max.)	8	A
$E_{AS}$	Single pulse avalanche energy (starting $T_J = 25\text{ }^{\circ}\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	1500	mJ

## 2 Electrical characteristics

( $T_{\text{case}} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)

**Table 4. Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(\text{BR})\text{DSS}}$	Drain-source breakdown voltage	$V_{\text{GS}} = 0\text{ V}$ , $I_{\text{D}} = 1\text{ mA}$	600			V
$I_{\text{DSS}}$	Zero gate voltage drain current	$V_{\text{GS}} = 0\text{ V}$ , $V_{\text{DS}} = 600\text{ V}$			10	$\mu\text{A}$
		$V_{\text{GS}} = 0\text{ V}$ , $V_{\text{DS}} = 600\text{ V}$ , $T_{\text{C}} = 125\text{ }^{\circ}\text{C}^{(1)}$			100	
$I_{\text{GSS}}$	Gate-body leakage current	$V_{\text{DS}} = 0\text{ V}$ , $V_{\text{GS}} = \pm 25\text{ V}$			$\pm 5$	$\mu\text{A}$
$V_{\text{GS(th)}}$	Gate threshold voltage	$V_{\text{DS}} = V_{\text{GS}}$ , $I_{\text{D}} = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{\text{DS(on)}}$	Static drain-source on-resistance	$V_{\text{GS}} = 10\text{ V}$ , $I_{\text{D}} = 33\text{ A}$		37	42	$\text{m}\Omega$

1. Specified by design, not tested in production.

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{\text{iss}}$	Input capacitance		-	5508	-	pF
$C_{\text{oss}}$	Output capacitance	$V_{\text{DS}} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{\text{GS}} = 0\text{ V}$	-	241	-	pF
$C_{\text{rss}}$	Reverse transfer capacitance		-	2.8	-	pF
$C_{\text{oss eq.}}^{(1)}$	Equivalent output capacitance	$V_{\text{DS}} = 0\text{ to }480\text{ V}$ , $V_{\text{GS}} = 0\text{ V}$	-	470	-	pF
$R_{\text{g}}$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	2	-	$\Omega$
$Q_{\text{g}}$	Total gate charge	$V_{\text{DD}} = 480\text{ V}$ , $I_{\text{D}} = 66\text{ A}$ , $V_{\text{GS}} = 0\text{ to }10\text{ V}$ (see Figure 14. Test circuit for gate charge behavior)	-	121	-	nC
$Q_{\text{gs}}$	Gate-source charge		-	26	-	nC
$Q_{\text{gd}}$	Gate-drain charge		-	61	-	nC

1.  $C_{\text{oss eq}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{\text{oss}}$  when  $V_{\text{DS}}$  increases from 0 to stated value.

**Table 6. Switching times**

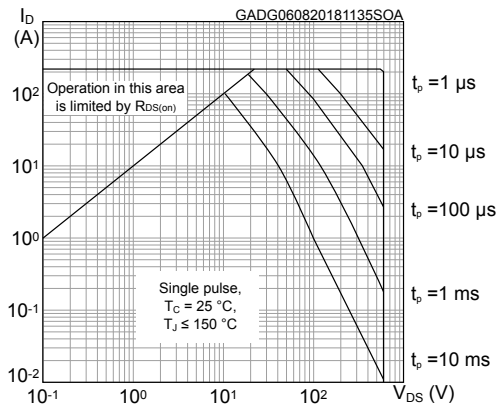
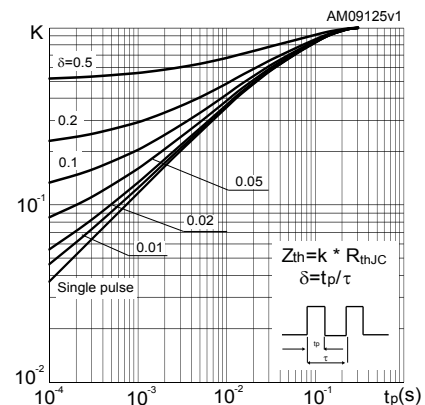
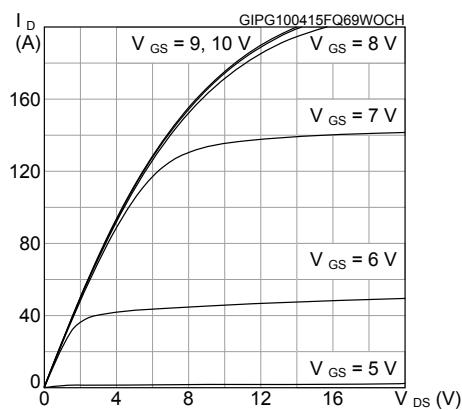
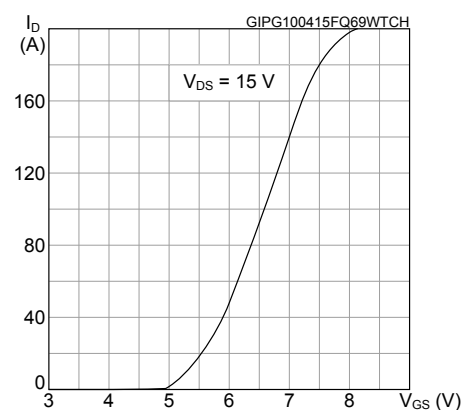
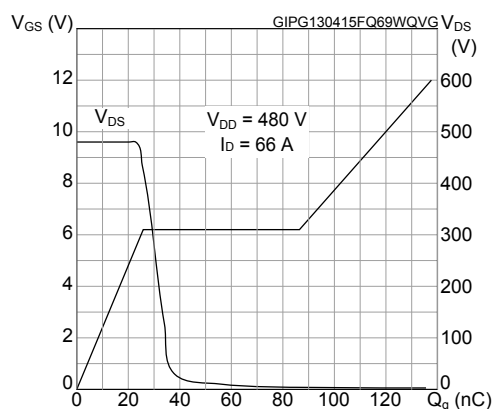
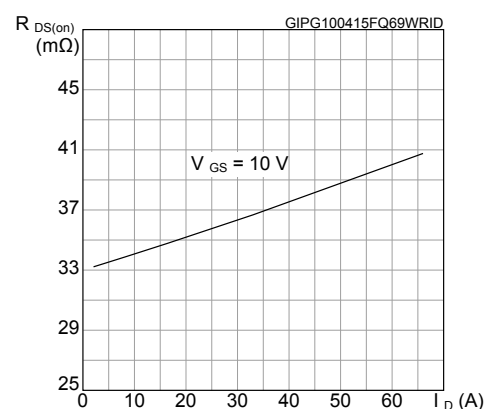
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{\text{d(on)}}$	Turn-on delay time	$V_{\text{DD}} = 300\text{ V}$ , $I_{\text{D}} = 33\text{ A}$ , $R_{\text{G}} = 4.7\text{ }\Omega$ , $V_{\text{GS}} = 10\text{ V}$	-	32	-	ns
$t_{\text{r}}$	Rise time		-	67	-	ns
$t_{\text{d(off)}}$	Turn-off delay time	(see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	112	-	ns
$t_{\text{f}}$	Fall time		-	10.4	-	ns

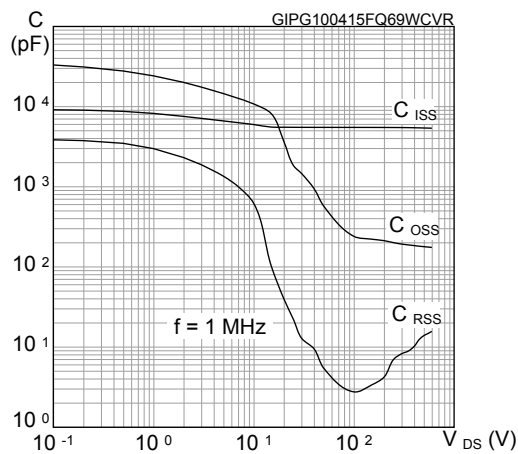
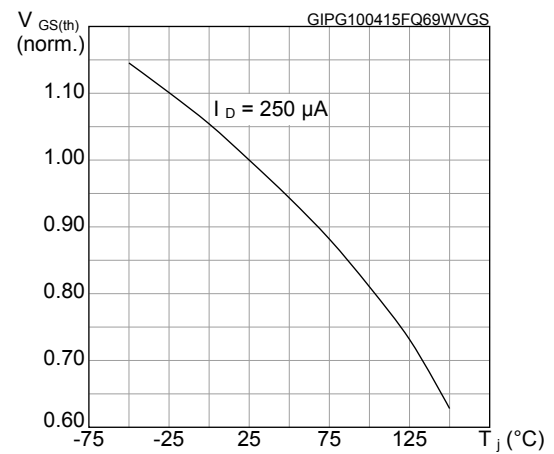
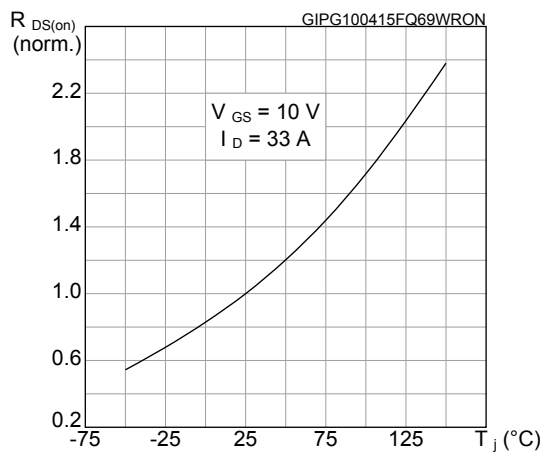
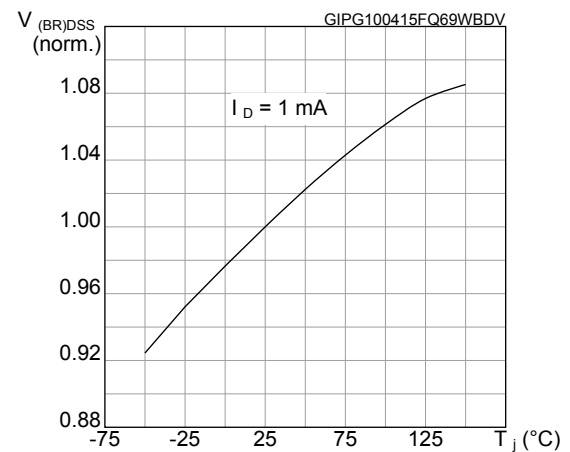
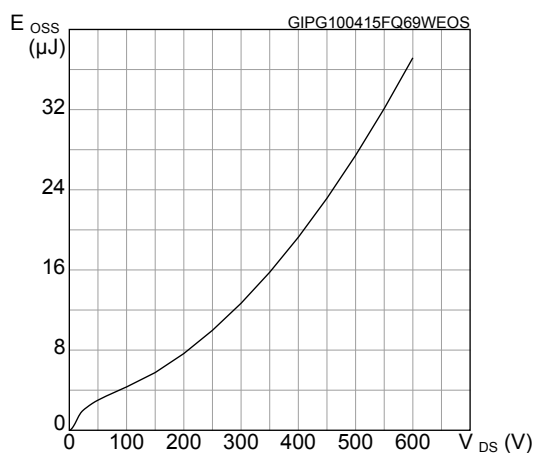
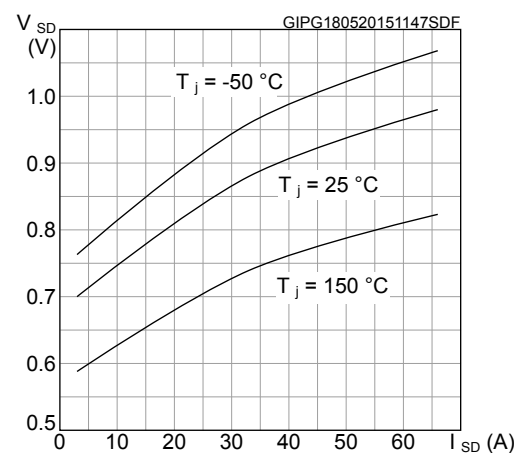
**Table 7. Source-drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		66	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		220	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$ , $I_{SD} = 66\text{ A}$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 66\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 480\text{ V}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	150		ns
$Q_{rr}$	Reverse recovery charge		-	0.75		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	10.5		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 66\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 480\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	250		ns
$Q_{rr}$	Reverse recovery charge		-	2.5		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	20.7		A

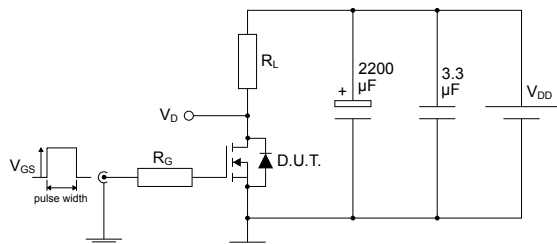
1. Pulse width is limited by safe operating area.
2. Pulse test: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

## 2.1 Electrical characteristics (curves)

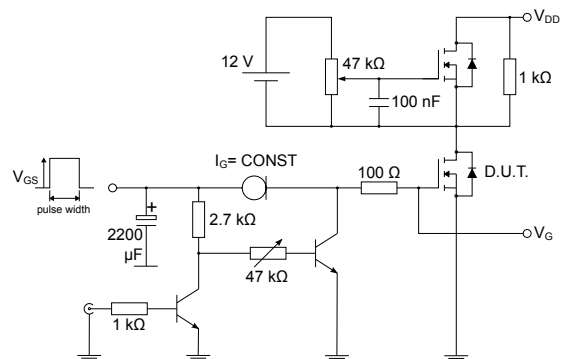
**Figure 1. Safe operating area**

**Figure 2. Normalized transient thermal impedance**

**Figure 3. Typical output characteristics**

**Figure 4. Typical transfer characteristics**

**Figure 5. Typical gate charge characteristics**

**Figure 6. Typical drain-source on-resistance**


**Figure 7. Typical capacitance characteristics**

**Figure 8. Normalized gate threshold vs temperature**

**Figure 9. Normalized on-resistance vs temperature**

**Figure 10. Normalized breakdown voltage vs temperature**

**Figure 11. Typical output capacitance stored energy**

**Figure 12. Typical reverse diode forward characteristics**


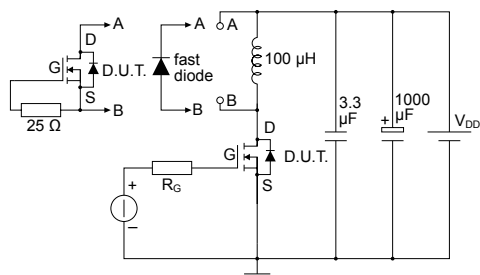
### 3 Test circuits

**Figure 13. Test circuit for resistive load switching times**


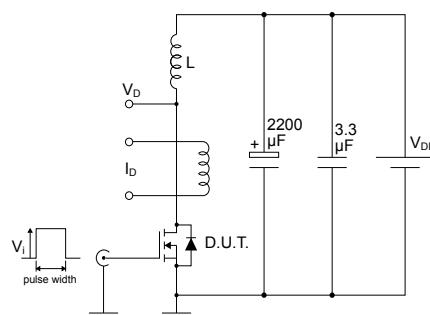
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**Figure 14. Test circuit for gate charge behavior**


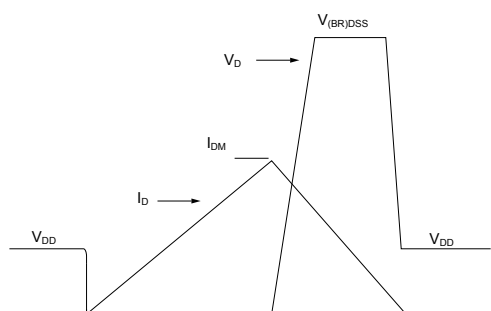
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**Figure 15. Test circuit for inductive load switching and diode recovery times**


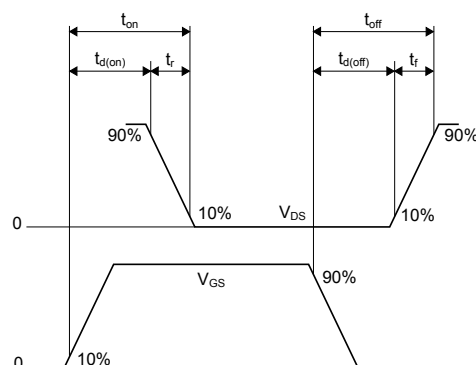
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**Figure 16. Unclamped inductive load test circuit**


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**Figure 17. Unclamped inductive waveform**


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**Figure 18. Switching time waveform**


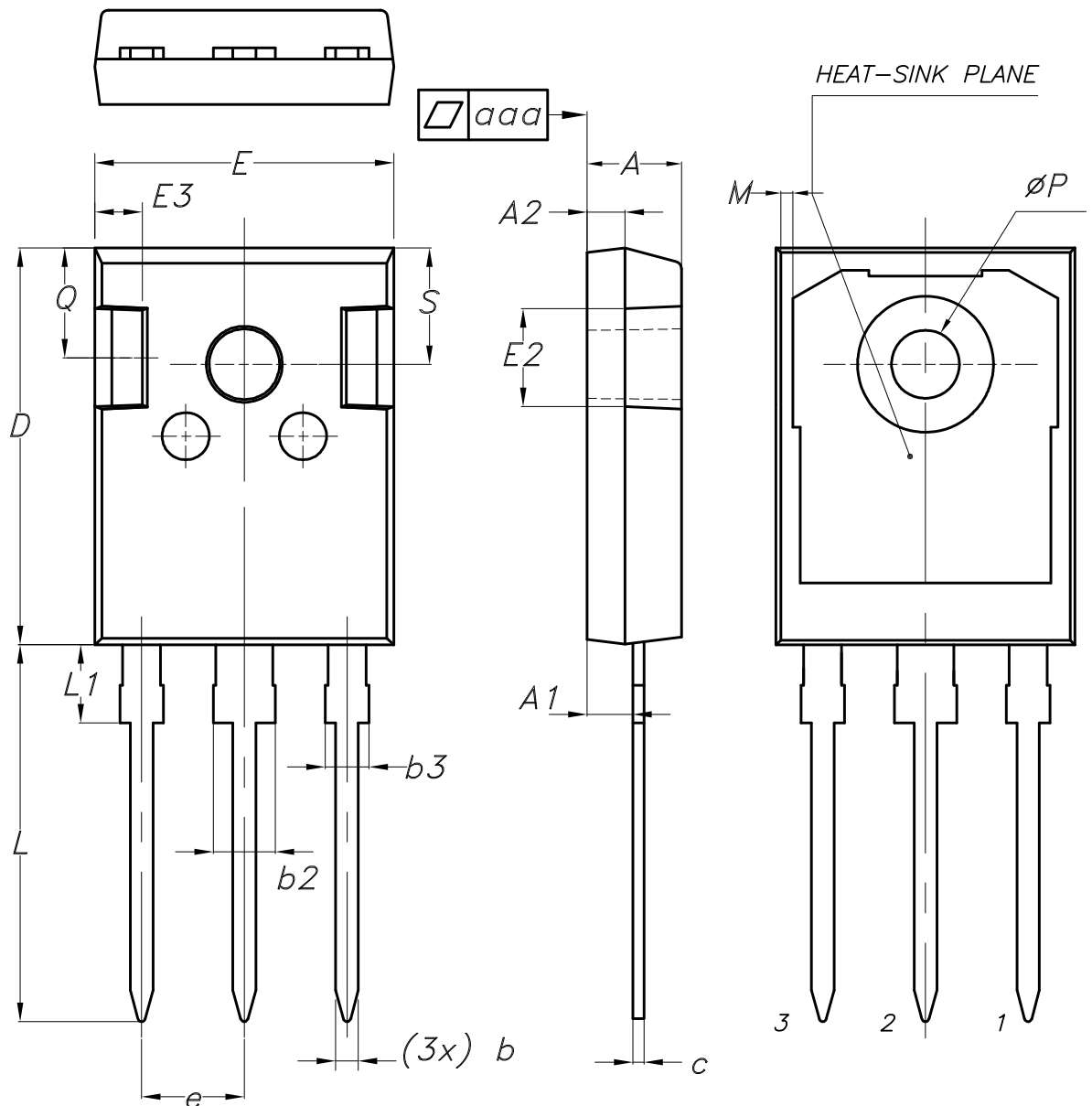
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## 4 Package information

To meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 4.1 TO-247 long leads package information

Figure 19. TO-247 long leads package outline



BACK VIEW

8463846\_6



**Table 8. TO-247 long leads package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16		1.26
b2			3.25
b3			2.25
c	0.59		0.66
D	20.90	21.00	21.10
E	15.70	15.80	15.90
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e	5.34	5.44	5.54
L	19.80	19.92	20.10
L1			4.30
M	0.35		0.95
P	3.50	3.60	3.70
Q	5.60		6.00
S	6.05	6.15	6.25
aaa		0.04	0.10

## Revision history

**Table 9. Document revision history**

Date	Version	Changes
07-Aug-2018	1	Initial release. The document status is production data.
20-Mar-2025	2	Updated <a href="#">Section 4.1: TO-247 long leads package information</a> . Minor text changes.

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